



### **60V Dual N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

40 A

#### **Features**

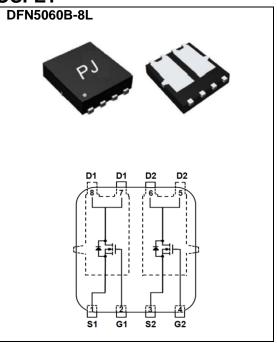
- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@20A<17m\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@10A<20mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN5060B-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0035 ounces, 0.092 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	60	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T <sub>C</sub> =25°C	l <sub>D</sub>	40		
	T <sub>C</sub> =100°C		25	Α	
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	160		
Power Dissipation	T <sub>C</sub> =25°C	Po	68.2	147	
	T <sub>C</sub> =100°C		34.1	W	
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	I <sub>D</sub>	7	^	
	T <sub>A</sub> =70°C		5.5	Α	
Power Dissipation	T <sub>A</sub> =25°C	Po	2.0	14/	
	T <sub>A</sub> =70°C		1.4	W	
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	45	mJ	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	2.2	°C/W	
	Junction to Ambient	$R_{\theta JA}$	73.5		

• Limited only By Maximum Junction Temperature





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static			•	•		
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1	1.7	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	13	17	mΩ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	-	16	20	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}$ =60V, $V_{GS}$ =0V	-	-	1	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> =30V, I <sub>D</sub> =10A, V <sub>GS</sub> =4.5V <sup>(Note 2,3)</sup>	-	13.5	-	nC
Gate-Source Charge	$Q_gs$		-	4.8	-	
Gate-Drain Charge	$Q_{gd}$		-	4.9	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	1574	-	pF
Output Capacitance	Coss		-	118	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	77	-	
Turn-On Delay Time	td <sub>(on)</sub>	\/ 45\/   40	-	11	-	
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}$ =15V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 2.3)	-	11	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	35	-	
Turn-Off Fall Time	t <sub>f</sub>		-	8.1	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	40	А
Diode Forward Current	I <sub>S</sub>					
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.68	1	V

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<a>2%</a>.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =30A,  $V_{DD}$ =25V,  $V_{GS}$ =10V, Starting  $T_J$ =25 $^{\circ}$ C.
- 7. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

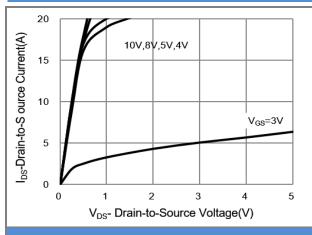
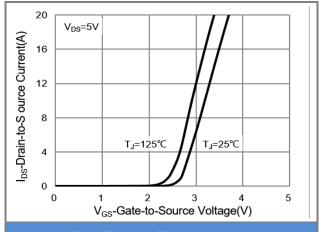


Fig.1 Output Characteristics



**Fig.2 Transfer Characteristics** 

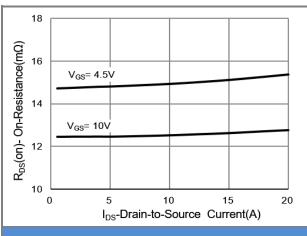


Fig.3 On-Resistance vs. Drain Current

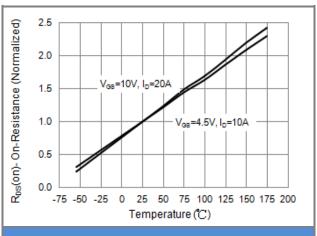
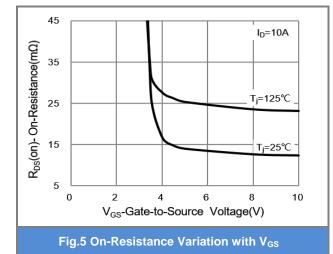


Fig.4 On-Resistance vs. Junction temperature



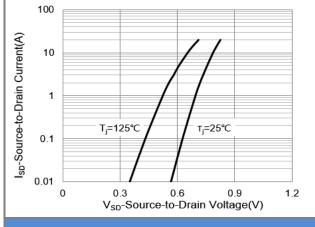


Fig.6 Source-Drain Diode Forward Voltage



1.6

1.4

1.2

1.0 0.8

0.6

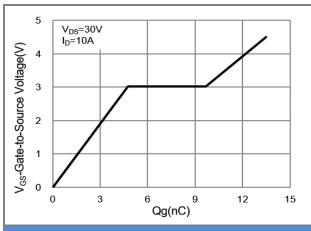
0.4

Vth-G-S Variance



# PJQ5866A-AU

#### TYPICAL CHARACTERISTIC CURVES



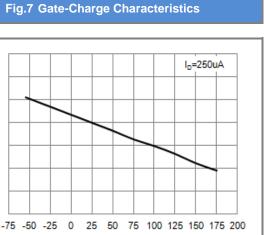
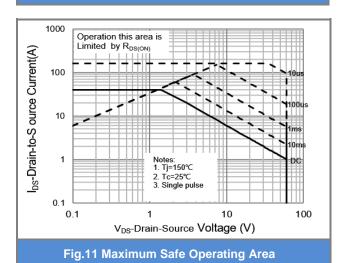


Fig.9 Threshold Voltage Variation with Temperature

Temperature (℃)



BVDSS-Breakdown Voltage (Normalized) 1.2 Ip=250uA 1.1 1.0 0.9 8.0 -75 -50 -25 0 25 50 75 100 125 150 175 200 Temperature (℃)

Fig.8 Breakdown Voltage Variation vs. Temperature

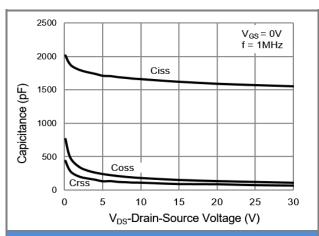


Fig.10 Capacitance vs. Drain-Source Voltage





#### **TYPICAL CHARACTERISTIC CURVES**

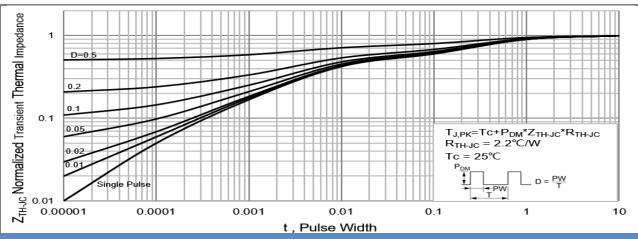


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

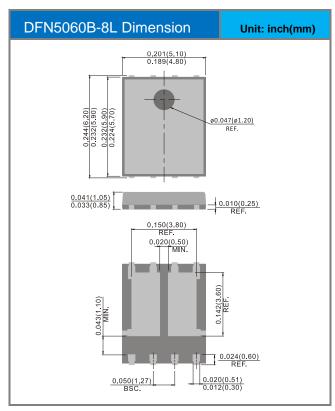


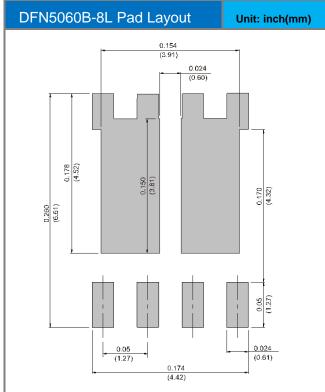


#### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5866A-AU_R2_000A1	DFN5060B-8L	3000pcs / 13" reel	Q5866A	Halogen free	

#### **Packaging Information & Mounting Pad Layout**









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